



60V N-CHANNEL ENHANCEMENT MODE MOSFET

100% Unclamped Inductive Switch (UIS) Test in Production

Totally Lead-Free & Fully RoHS Compliant (Notes 1 & 2) Halogen and Antimony Free. "Green" Device (Note 3)

Low R_{DS(ON)} – Ensures On State Losses Are Minimized

Product Summary

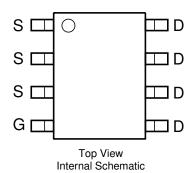
BV _{DSS}	R _{DS(ON)} max	I _D max T _A = +25°C		
c0)/	9.5mΩ @ V _{GS} = 10V	10.8A		
60V	12mΩ @ V _{GS} = 4.5V	9.6		

Description and Applications

This new generation MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$) and yet maintain superior switching performance, making it ideal for high-efficiency power management applications.

- Power Management Functions
- DC-DC Converters
- Backlighting





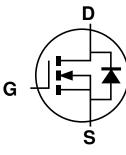
Mechanical Data

Features and Benefits

High Conversion Efficiency

Excellent Q_{gd} x R_{DS(ON)} Product (FOM) Advanced Technology for DC-DC Converters

- Case: SO-8
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Finish Matte Tin Annealed over Copper Leadframe; Solderable per MIL-STD-202, Method 208 ⁽³⁾
- Weight: 0.074 grams (Approximate)



Equivalent circuit

Ordering Information (Note 4)

Part Number	Case	Packaging
DMT6009LSS-13	SO-8	2,500/Tape & Reel

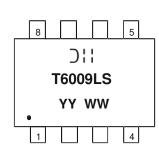
Notes: 1. No purposely added lead. Fully EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant.

2. See http://www.diodes.com/quality/lead_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green"

and Lead-free. 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.

4. For packaging details, go to our website at http://www.diodes.com/products/packages.html.

Marking Information



);; = Manufacturer's Marking T6009LS = Product Type Marking Code YYWW = Date Code Marking YY or \overline{YY} = Year (ex: 15 = 2015) WW = Week (01 to 53)



Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Units	
Drain-Source Voltage			V _{DSS}	60	V	
Gate-Source Voltage			V _{GSS}	±20	V	
Continuous Drain Current (Note 6) V _{GS} = 10V	Steady State	T _A = +25°C T _A = +70°C	ID	10.8 8.6	A	
	t<10s	T _A = +25°C T _A = +70°C	ID	14.4 11.5	A	
Maximum Continuous Body Diode Forward Current (Note 6)			ls	3	A	
Pulsed Drain Current (10µs Pulse, Duty Cycle = 1%)			I _{DM}	60	А	
Avalanche Current, L = 0.1mH			I _{AS}	25	А	
Avalanche Energy, L = 0.1mH			E _{AS}	31.5	mJ	

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		PD	1.25	W
Thermal Resistance. Junction to Ambient (Note 5)	Steady State	Р	100	°C/W
merinal Resistance, Junction to Ambient (Note 5)	t<10s	R _θ JA	55.5	°C/W
Total Power Dissipation (Note 6)		PD	1.6	W
Thermal Desistance, Junction to Ambient (Nate 6)	Steady State	Б	75	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t<10s	R ₀ JA	42	°C/W
Thermal Resistance, Junction to Case (Note 6)		$R_{\theta JC}$	12	°C/W
Operating and Storage Temperature Range		TJ, TSTG	-55 to +150	°C

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

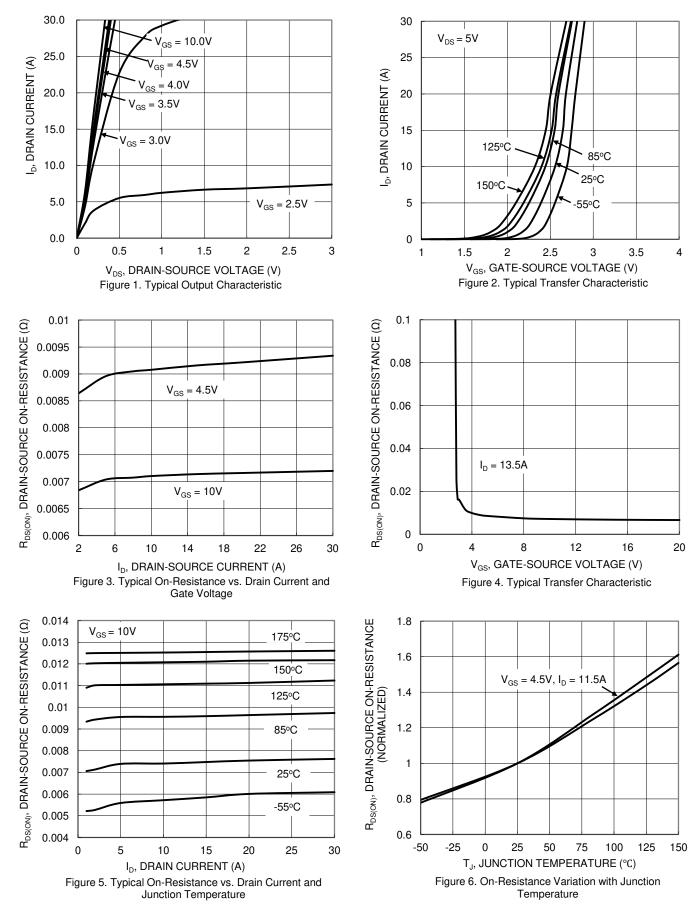
Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 7)	Symbol		тур	IWAA	Onit	Test condition	
Drain-Source Breakdown Voltage	BV _{DSS}	60	-	-	V	V _{GS} = 0V, I _D = 250µA	
Zero Gate Voltage Drain Current	IDSS	-	-	1	μA	$V_{DS} = 48V, V_{GS} = 0V$	
Gate-Source Leakage	IGSS	-	-	±100	nA	$V_{GS} = \pm 16V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 7)						<u> </u>	
Gate Threshold Voltage	V _{GS(TH)}	0.7	-	2	V	$V_{DS} = V_{GS}, I_D = 250 \mu A$	
Static Drain-Source On-Resistance		-	7.2	9.5	mΩ	V _{GS} = 10V, I _D = 13.5A	
Static Drain-Source On-Resistance	R _{DS} (ON)	-	9	12		V _{GS} = 4.5V, I _D = 11.5A	
Diode Forward Voltage	V _{SD}	-	0.9	1.2	V	$V_{GS} = 0V, I_{S} = 20A$	
DYNAMIC CHARACTERISTICS (Note 8)							
Input Capacitance	C _{iss}	-	1,925	-			
Output Capacitance	Coss	-	438	-	pF	$V_{DS} = 30V, V_{GS} = 0V,$ f = 1MHz	
Reverse Transfer Capacitance	C _{rss}	-	41	-			
Gate Resistance	R _G	-	1.7	-	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1MHz$	
Total Gate Charge (V _{GS} = 10V)	Qg	-	33.5	-			
Total Gate Charge (V _{GS} = 4.5V)	Qg	-	15.6	-	nC	$V_{DS} = 30V, I_D = 13.5A$	
Gate-Source Charge	Qgs	-	4.7	-	no		
Gate-Drain Charge	Q _{qd}	-	5.3	-			
Turn-On Delay Time	t _{D(ON)}	-	4.5	-		$\label{eq:VDD} \begin{split} V_{DD} &= 30V, \ V_{GS} = 10V, \\ R_G &= 6\Omega, \ I_D = 13.5A \end{split}$	
Turn-On Rise Time	t _R	-	8.6	-			
Turn-Off Delay Time	t _{D(OFF)}	-	35.9	-	ns		
Turn-Off Fall Time	tF	-	15.7	-			
Body Diode Reverse Recovery Time	t _{RR}	-	18.2	-	ns		
Body Diode Reverse Recovery Charge	Q _{RR}	-	33.1	-	nC	I _F = 13.5A, di/dt = 400A/μs	

 Device mounted on FR-4 substrate PC board, 2oz. copper, with minimum recommended pad layout.
Device mounted on FR-4 substrate PC board, 2oz. copper, with 1inch square copper plate.
Short duration pulse test used to minimize self-heating effect. Notes:

8. Guaranteed by design. Not subject to product testing.



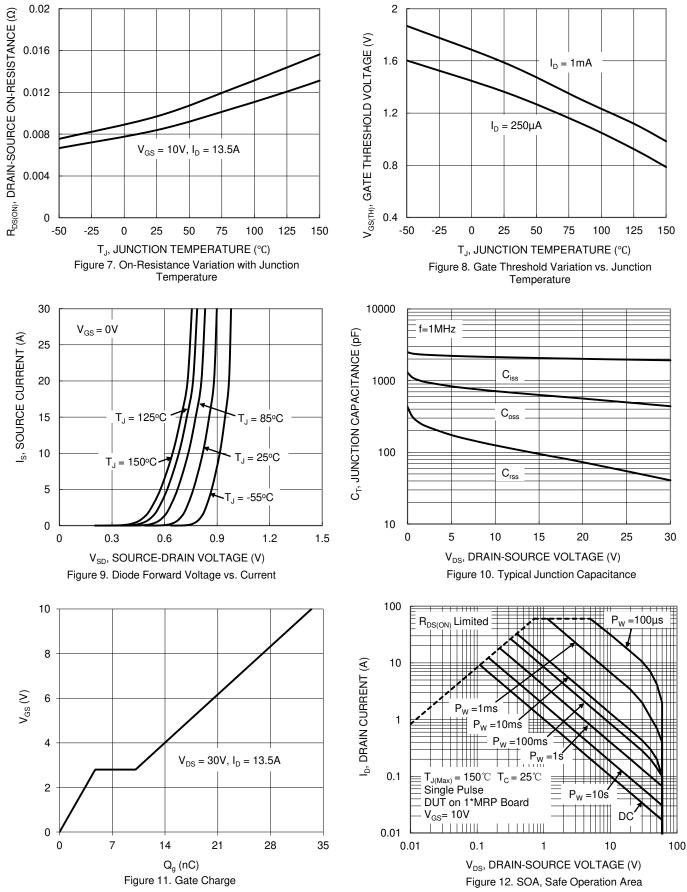
DMT6009LSS



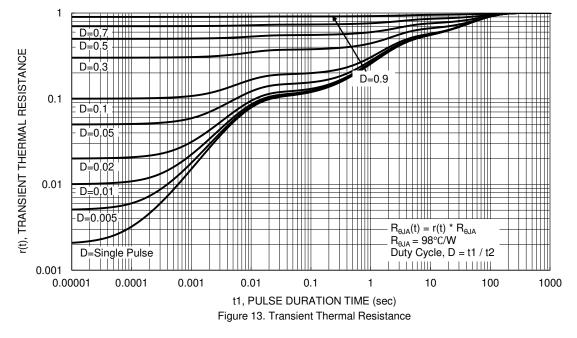
DMT6009LSS Document number: DS38289 Rev. 1 - 2



DMT6009LSS

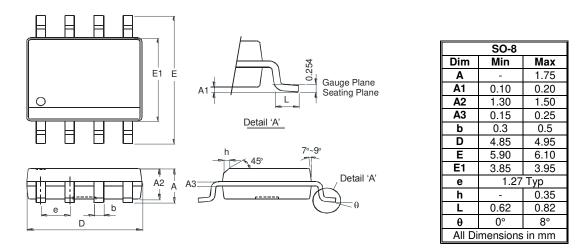






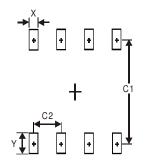
Package Outline Dimensions

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version



Suggested Pad Layout

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
Х	0.60
Y	1.55
C1	5.4
C2	1.27



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